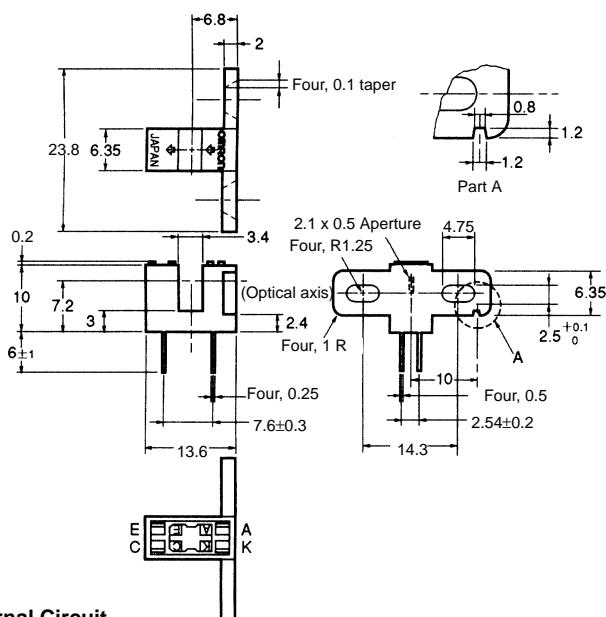
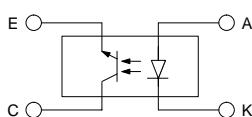


## ■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.2
3 < mm ≤ 6	±0.24
6 < mm ≤ 10	±0.29
10 < mm ≤ 18	±0.35
18 < mm ≤ 30	±0.42

Terminal No.	Name
A	Anode
K	Cathode
C	Collector
E	Emitter

## ■ Features

- General-purpose model with a 3.4-mm-wide slot.
- PCB mounting type.
- High resolution with a 0.5-mm-wide aperture.
- Screw-mounting possible.

## ■ Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Rated value
Emitter	Forward current	I <sub>F</sub>	50 mA (see note 1)
	Pulse forward current	I <sub>FP</sub>	1 A (see note 2)
	Reverse voltage	V <sub>R</sub>	4 V
Detector	Collector-Emitter voltage	V <sub>CEO</sub>	30 V
	Emitter-Collector voltage	V <sub>ECO</sub>	---
	Collector current	I <sub>C</sub>	20 mA
	Collector dissipation	P <sub>C</sub>	100 mW (see note 1)
Ambient temperature	Operating	T <sub>opr</sub>	-25°C to 85°C
	Storage	T <sub>stg</sub>	-40°C to 100°C
Soldering temperature		T <sub>sol</sub>	260°C (see note 3)

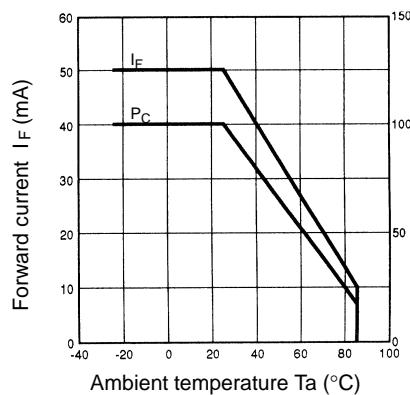
- Note:
- Refer to the temperature rating chart if the ambient temperature exceeds 25°C.
  - The pulse width is 10 µs maximum with a frequency of 100 Hz.
  - Complete soldering within 10 seconds.

## ■ Electrical and Optical Characteristics (Ta = 25°C)

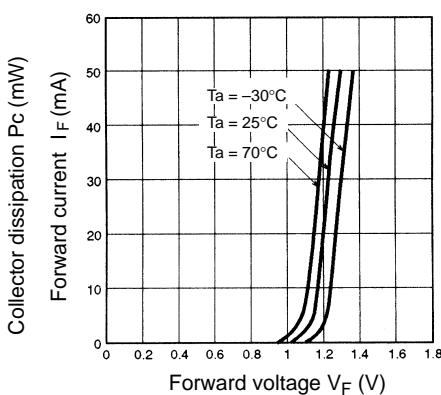
Item	Symbol	Value	Condition
Emitter	Forward voltage	V <sub>F</sub>	1.2 V typ., 1.5 V max. I <sub>F</sub> = 30 mA
	Reverse current	I <sub>R</sub>	0.01 µA typ., 10 µA max. V <sub>R</sub> = 4 V
	Peak emission wavelength	λ <sub>P</sub>	940 nm typ. I <sub>F</sub> = 20 mA
Detector	Light current	I <sub>L</sub>	1.9 mA min., 14 mA max. I <sub>F</sub> = 20 mA, V <sub>CE</sub> = 10 V
	Dark current	I <sub>D</sub>	2 nA typ., 200 nA max. V <sub>CE</sub> = 10 V, 0 lx
	Leakage current	I <sub>LEAK</sub>	---
	Collector-Emitter saturated voltage	V <sub>CE</sub> (sat)	0.1 V typ., 0.4 V max. I <sub>F</sub> = 20 mA, I <sub>L</sub> = 0.1 mA
	Peak spectral sensitivity wavelength	λ <sub>P</sub>	850 nm typ. V <sub>CE</sub> = 10 V
Rising time	tr	4 µs typ.	V <sub>CC</sub> = 5 V, R <sub>L</sub> = 100 Ω, I <sub>L</sub> = 5 mA
Falling time	tf	4 µs typ.	V <sub>CC</sub> = 5 V, R <sub>L</sub> = 100 Ω, I <sub>L</sub> = 5 mA

## ■ Engineering Data

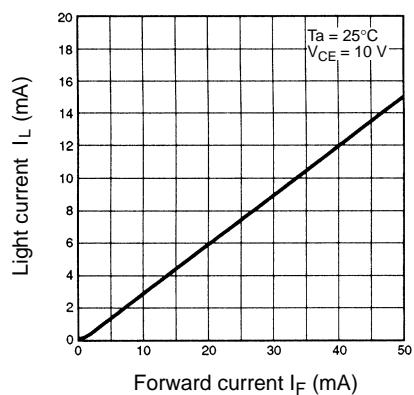
**Forward Current vs. Collector Dissipation Temperature Rating**



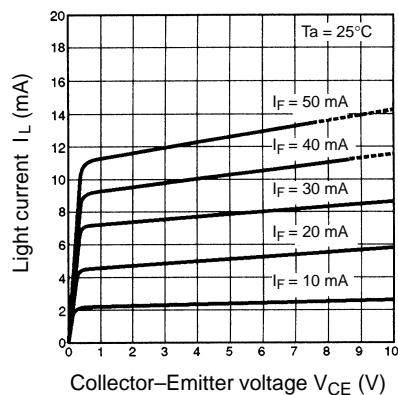
**Forward Current vs. Forward Voltage Characteristics (Typical)**



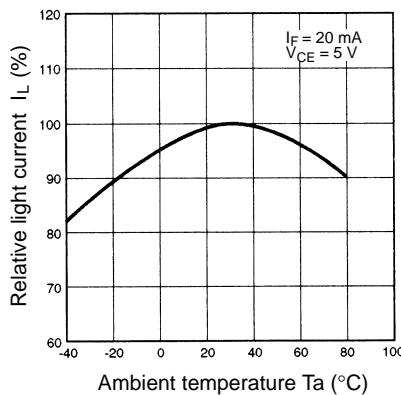
**Light Current vs. Forward Current Characteristics (Typical)**



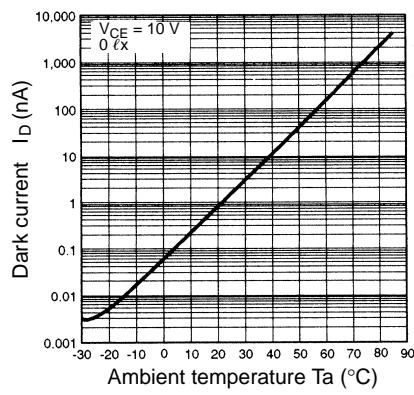
**Light Current vs. Collector-Emitter Voltage Characteristics (Typical)**



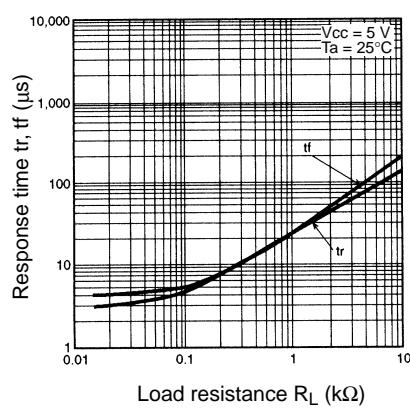
**Relative Light Current vs. Ambient Temperature Characteristics (Typical)**



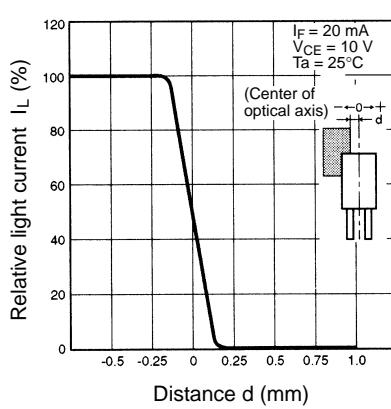
**Dark Current vs. Ambient Temperature Characteristics (Typical)**



**Response Time vs. Load Resistance Characteristics (Typical)**



**Sensing Position Characteristics (Typical)**



**Response Time Measurement Circuit**

